

RJK2054DPC

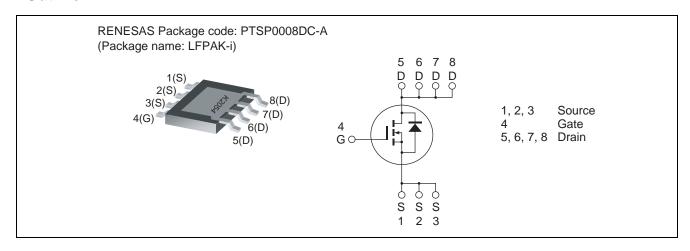
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1868-0100 Rev.1.00 Dec 08, 2009

Features

- Low on-resistance $R_{DS(on)}=0.075~\Omega~typ.~(at~I_D=8.5~A,~V_{GS}=10~V,~Ta=25^{\circ}C)$
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	200	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	17	Α
Drain peak current	I _{D (pulse)} Note1	34	A
Body-drain diode reverse drain current	I _{DR}	17	Α
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	34	Α
Avalanche current	I _{AP} Note3	10	A
Avalanche energy	E _{AR} Note3	6.6	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C

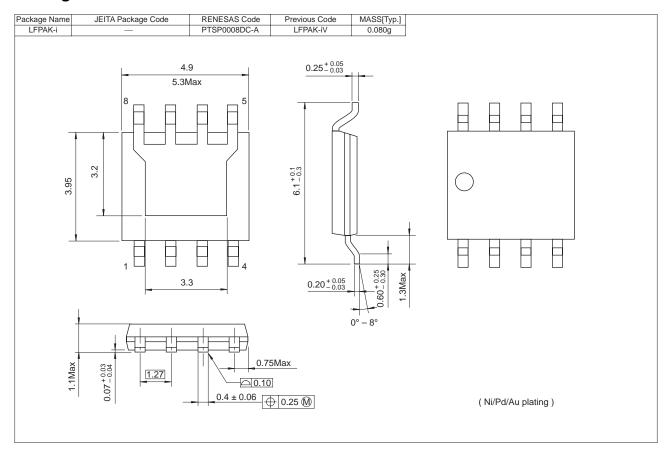
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.5	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	0.075	0.098	Ω	$I_D = 8.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	1700	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	180	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	37	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	21	_	ns	$I_D = 8.5 A$
Rise time	t _r	_	13	_	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	_	40	_	ns	$R_L = 11.8 \Omega$
Fall time	t _f	_	13	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	27.3	_	nC	V _{DD} = 160 V
Gate to source charge	Qgs	_	8.6	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd	_	7.8	_	nC	I _D = 17 A
Body-drain diode forward voltage	V_{DF}	_	0.82	1.25	V	$I_F = 17 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}	_	110	_		$I_F = 17 \text{ A}, V_{GS} = 0$ dt/dt = 100 A/ μ s

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK2054DPC-00-J0	2500 pcs	Taping

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